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Suppl. IDS
Y. Robinson
6/10/03

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: PARIKH et al.

Serial No. 09/911,155

Group Art Unit: 2811

Filed: July 23, 2001

Title: GALLIUM NITRIDE BASED DIODES WITH LOW FORWARD VOLTAGE AND LOW REVERSE CURRENT OPERATION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

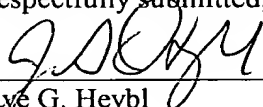
This certification is being made for the Information Disclosure Statement accompanying this certification. Applicants submit a copy of each of the references listed on the attached supplemental PTO-1449 (Modified) form for consideration by the Examiner.

I, the person signing below certify that:

(a) each item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement (37 C.F.R. § 1.97(e)(1)); or

(b) no item of information contained in the information disclosure statement, to the knowledge of the person signing the certification after making reasonable inquiry, was known to any individual designated in § 1.56(c) more than three months prior to the filing of the statement. 37 C.F.R. § 1.97(e)(2).

Respectfully submitted,

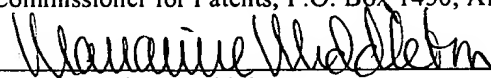

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May 21, 2003

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CERTIFICATE OF MAILING

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A circular stamp from the Office of Intellectual Property (OIP). The text "OIP" is at the top, "JCS" is at the top right, "MAY 28 2003" is in the center, and "PATENT & TRADE MARK OFFICE" is around the bottom.

U.S. PATENT DOCUMENTS

RECEIVED
MAY 20 1993
TECHNICAL SERVICES DIVISION

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	1	ZHANG A P et al, "COMPARISON OF GAN P-I-N AND SCHOTTKY RECTIFIER PERFORMANCE", IEEE TRANSACTIONS ON ELECTRON DEVICES, IEEE INC. NEW YORK, US, Vol. 48, No. 3, March 2001 (2001-03), p. 407-411, XP001038984 ISSN, 0018-9383
	2	MOHAMMAD S N et al. "NEAR-IDEAL PLATINUM-GaN SCHOTTKY DIODES", ELECTRONICS LETTERS, IEE STEVENAGE, GB, Vol. 32, No. 6, 3/14/96, p. 598-599, XP006004867, ISSN, 0013-5194.
	3	SCHMITZ A C A et al., "METAL CONTACTS TO N-TYPE GaN", III-V NITRIDES AND SILICON CARBIDE, FORT COLLINS, CO, USA, 1997, Vol. 27, No. 4, p. 255-260, XP008016192, JOURNAL OF ELECTRONIC MATERIALS, 4/1998, TMS, USA, ISSN, 0361-5235
Examiner	Date Considered	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.